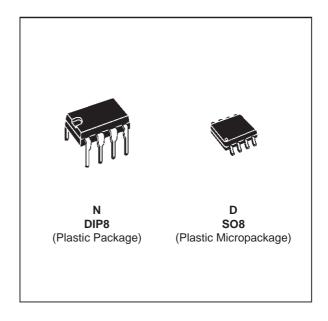


TSH11

120MHz BANDWIDTH MOS INPUT SINGLE OPERATIONAL AMPLIFIER

VERY LOW INPUT CURRENT : 2pA typGAIN BANDWIDTH PRODUCT : 120MHz

■ UNITY GAIN STABLE
■ SLEW RATE: 150V/µs
■ STANDARD PIN OUT



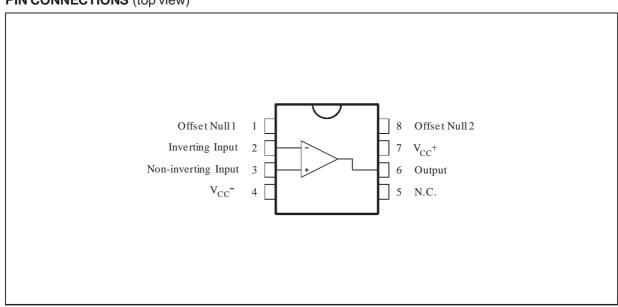
DESCRIPTION

The TSH11 is a low cost wide bandwidth single operational amplifier featuring extremely low input current of 2pA typ. Other features as unity gain stability, fast settling time and high linearity make it suitable for many applications requiring speed and very high input impedance as photo cell amplifier, high input impedance buffer, Fet probe, high speed precision integrator, sample and hold circuit...

ORDER CODES

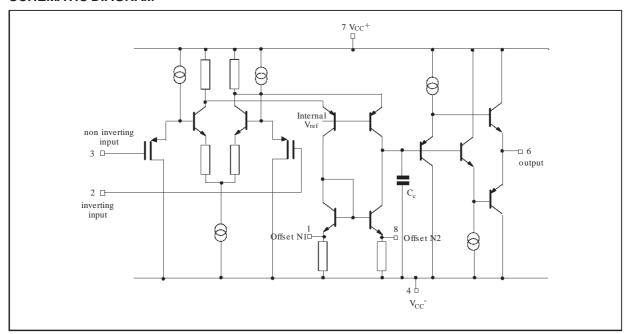
Part	Temperature	Package		
Number	Range	N D		
TSH11I	-40°C, 125°C	•	•	

PIN CONNECTIONS (top view)

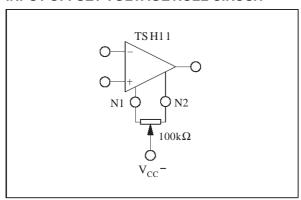


June 1998 1/6

SCHEMATIC DIAGRAM



INPUT OFFSET VOLTAGE NULL CIRCUIT



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	±7	V
V _{id}	Differential Input Voltage	±5	V
Vi	Input Voltage Range	±5	V
I _{in}	Current On Offset Null Pins	±20	mA
T _{oper}	Operating Free-Air Temperature Range TSH11C TSH11I TSH11M	0°C +70 -40°C +105 -55°C +125	°C

OPERATING CONDITIONS

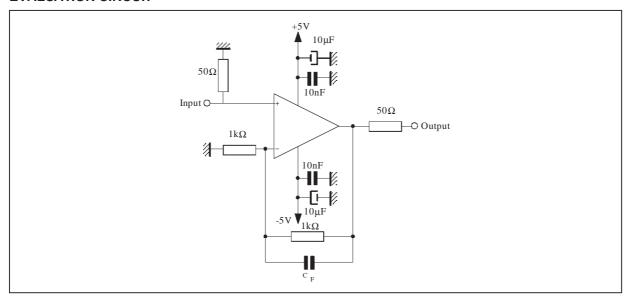
Symbol	Parameter	Value	Unit
Vcc	Supply Voltage	±3 to ±6	V
V _{ic}	Common Mode Input Voltage Range	V _{CC} ⁻ to V _{CC} ⁺ -3	V

2/6

ELECTRICAL CHARACTERISTICS $V_{CC} = \pm 5V$, $T_{amb} = 25^{\circ}C$ (unless otherwise specified)

Symbol	Parameter		Min.	Тур.	Max.	Unit
Vio	Input Offset Voltage			3	15	mV
DV _{io}	$\begin{array}{c} \text{Input Offset Voltage Drift} \\ T_{\text{min}} \leq T_{\text{amb}} \leq T_{\text{max}} \end{array}$			20		μV/°C
l _{ib}	Input Bias Current			2	300	pA
l _{io}	Input Offset Current			2	200	pА
Icc	Supply Current, no load	$V_{CC} = \pm 5V$		20	40	mA
A_{vd}	Large Signal Voltage Gain V _o = ±2.5V	R _L = 100Ω	200	800		V/V
V_{icm}	Input Common Mode Voltage Ran	ige	-5 to +2	-5.5 to +2.5		V
CMR	Common Mode Rejection Ratio	$V_{ic} = V_{icm \ min.}$	55	95		dB
SVR	Supply Voltage Rejection Ratio $V_{CC} = \pm 5V$ to $\pm 3V$		45	65		dB
Vo	Output Voltage	$R_L = 100\Omega$	± 2.5	+3.5 -3.7		V
lo	Output Short Circuit Current $V_{id} = \pm 1V$, $V_0 = 0V$			±70		mA
GBP	Gain Bandwidth Product $A_{VCL} = 100$, $R_L = 100\Omega$, $f = 7.5$	5MHz		120		MHz
SR	Slew Rate $V_{in} = \pm 2V$, $A_{VCL} = 1$, $R_L = 1009$	Ω		150		V/μs
en	Equivalent Input Voltage Noise	f = 1MHz		20		$\frac{\text{nV}}{\sqrt{\text{Hz}}}$
Øm	Phase Margin $A_{VM} = 1$, $R_L = 100\Omega$, $C_L = 15pI$	=		40		Degrees

EVALUATION CIRCUIT



PRINTED CIRCUIT LAYOUT

As for any high frequency device, a few rules must be observed when designing the PCB to get the best performances from your this speed op amp.

From the most to the least important points:

- Each power supply lead has to be bypassed to ground with a 10nF ceramic capacitor very close to the device and a 10μF tantalum capacitor.
- To provide low inductance and low resistance common return, use a ground plane or common point return for power and signal.
- All leads must be wide and as short as possible especially for op amp inputs. This is in order to decrease parasitic capacitance and

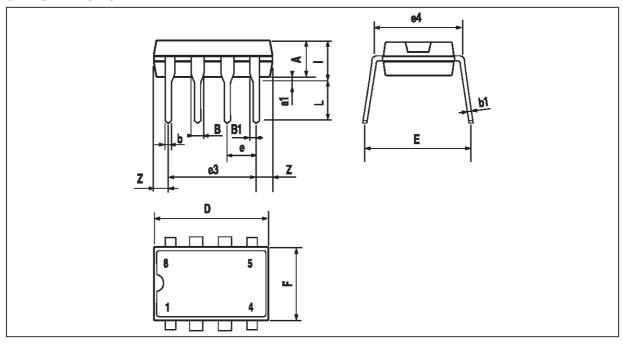
inductance.

- Use small resistor values to decrease time constant with parasitic capacitance.
- Choose component sizes as small as possible (SMD).
- On output, decrease capacitor load so as to avoid circuit stability being degraded which may cause oscillation. One can also add a serial resistor in order to minimise its influence.
- One can add in parallel with feedback resistor a few pF ceramic capacitor C_F adjusted to optimize the settling time.

4/6

PACKAGE MECHANICAL DATA

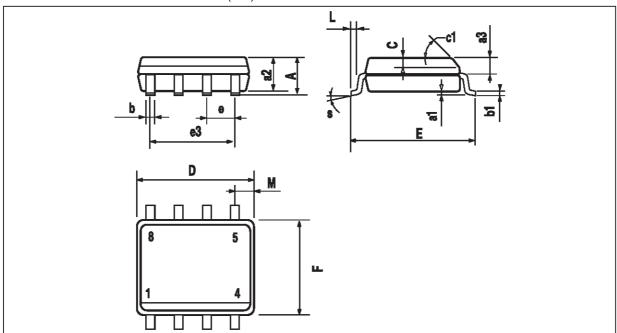
8 PINS - PLASTIC DIP



Dimensions	Millimeters			Inches		
Dimensions	Min.	Тур.	Max.	Min.	Тур.	Max.
А		3.32			0.131	
a1	0.51			0.020		
В	1.15		1.65	0.045		0.065
b	0.356		0.55	0.014		0.022
b1	0.204		0.304	0.008		0.012
D			10.92			0.430
Е	7.95		9.75	0.313		0.384
е		2.54			0.100	
e3		7.62			0.300	
e4		7.62			0.300	
F			6.6			0260
i			5.08			0.200
L	3.18		3.81	0.125		0.150
Z			1.52			0.060

PACKAGE MECHANICAL DATA

8 PINS - PLASTIC MICROPACKAGE (SO)



Dimensions		Millimeters		Inches		
Dilliensions	Min.	Тур.	Max.	Min.	Тур.	Max.
А			1.75			0.069
a1	0.1		0.25	0.004		0.010
a2			1.65			0.065
a3	0.65		0.85	0.026		0.033
b	0.35		0.48	0.014		0.019
b1	0.19		0.25	0.007		0.010
С	0.25		0.5	0.010		0.020
c1			45°	(typ.)		•
D	4.8		5.0	0.189		0.197
E	5.8		6.2	0.228		0.244
е		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.150		0.157
L	0.4		1.27	0.016		0.050
М			0.6			0.024
S	8° (max.)					

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47/